

Dual N-channel MOSFET

FCAB22710L Datasheet

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1. GENERAL DESCRIPTION

Dual N-channel MOSFET.

2. FEATURES

- Source-source On-state Resistance: RSS(on) typ = 7.5 m Ω (VGS = 3.8 V)
- · CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1)

3. MARKING SYMBOL: WJ

4. PACKAGING

Embossed type (Thermo-compression sealing): 10,000 pcs / reel (standard)

5. ABSOLUTE MAXIMUM RATINGS Ta = 25 °C

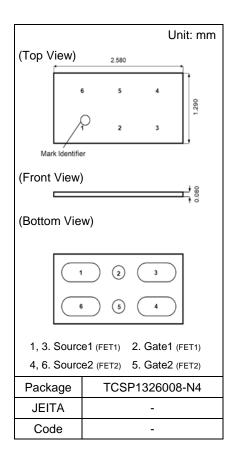
| Parameter | Symbol | Rating | Unit | |
|---|-----------|----------|---------------|----|
| Source-source Voltage | | VSS | 20 | V |
| Gate-source Voltage | | VGS | ± 12 | V |
| | DC *1 | IS1 | 6.1 | |
| Source Current | DC *2 | IS2 | 10.9 | Α |
| | DC *3 | IS3 | 15.0 | A |
| | Pulsed *4 | ISp | 61.0 | |
| | DC *1 | PD1 | 0.51 | |
| Total Power Dissipation | DC *2 | PD2 | 1.60 | W |
| | DC *3 | PD3 | 3.00 | |
| Operating Junction and Storage Temperature Range | | Tj, Tstg | - 55 to + 150 | °C |

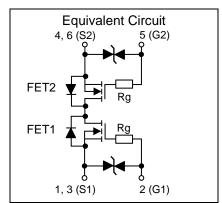
6. THERMAL CHARACTERISTICS Ta = 25 °C

| Parameter | Symbol | Rating | Unit |
|---------------------------|---------|--------|------|
| | Rth1 *1 | 245 | |
| Thermal Resistance (ch-a) | Rth2 *2 | 78 | °C/W |
| | Rth3 *3 | 41 | |

Note *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board partially covered with copper pad (22 mm² area, 36 µm thickness).

- *2 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board fully covered with copper pad (602 mm² area, 36 µm thickness).
- *3 Mounted on ceramic board (70 mm x 70 mm x t1.0 mm).
- *4 $t = 10 \mu s$, Duty Cycle $\leq 1 \%$.







7. ELECTRICAL CHARACTERISTICS Ta = 25 °C ± 3 °C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|-----------------------------------|----------|----------------------------|------|------|------|-------|
| Source-source Breakdown Voltage | VSSS | IS = 1 mA, VGS = 0 V | 12 | | | V |
| Zero Gate Voltage Source Current | ISSS | VSS = 20 V, VGS = 0 V | | | 1 | μΑ |
| Cata aguras Lagkaga Current | IGSS1 | VGS = ± 8 V, VSS = 0 V | | | ± 10 | |
| Gate-source Leakage Current | IGSS2 | VGS = ± 5 V, VSS = 0 V | | | ± 1 | μA |
| Gate-source Threshold Voltage | Vth | IS = 0.54 mA, VSS = 10 V | 1.30 | 1.85 | 2.35 | V |
| | RSS(on)1 | IS = 3.05 A, VGS = 4.5 V | 3.9 | 5.5 | 7.5 | mΩ |
| Source-source On-state Resistance | RSS(on)2 | IS = 3.05 A, VGS = 3.8 V | 5.3 | 7.5 | 12.5 | 11177 |
| | RSS(on)3 | IS = 0.20 A, VGS = 3.1 V | 5.4 | 16.5 | 70.0 | |
| Body Diode Forward Voltage | VF(s-s) | IF = 3.05 A, VGS = 0 V | | 0.8 | 1.2 | V |
| Turn-on Delay Time *1,*2 | td(on) | VDD = 10 V, VGS = 0 to 4 V | | 62 | | 200 |
| Rise Time *1, *2 | tr | IS = 3.05 A | | 240 | | ns |
| Turn-off Delay Time *1,*2 | td(off) | VDD = 10 V, VGS = 4 to 0 V | | 155 | | 20 |
| Fall Time *1, *2 | tf | IS = 3.05 A | | 140 | | ns |
| Total Gate Charge *1 | Qg | VDD = 10 V | | 17.5 | | |
| Gate-source Charge *1 | Qgs | VGS = 0 to 4 V | | 6.5 | | nC |
| Gate-drain Charge *1 | Qgd | IS = 6.1 A | | 6.5 | | |
| Gate Resistance *1 | Rg | f = 1 MHz | | 24.5 | | Ω |

(MOSFET: FET1)

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---------------------------------|--------|---|-----|------|-----|------|
| Input Capacitance *1 | Ciss | | | 2320 | | |
| Output Capacitance *1 | Coss | VSS = 10 V, f = 1 kHz VGS1 = 0 V. VGS2 = 6 V | | 265 | | pF |
| Reverse Transfer Capacitance *1 | Crss | V 001 = 0 V, V 002 = 0 V | | 205 | | |

(MOSFET: FET2)

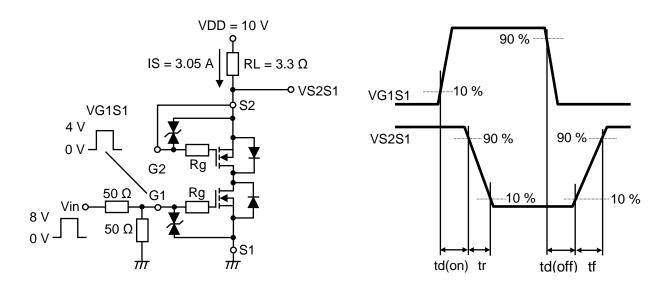
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---------------------------------|--------|---|-----|------|-----|------|
| Input Capacitance *1 | Ciss | | | 2320 | | |
| Output Capacitance *1 | Coss | VSS = 10 V, f = 1 kHz VGS2 = 0 V. VGS1 = 6 V | | 265 | | pF |
| Reverse Transfer Capacitance *1 | Crss | 1 1352 = 3 1, 1331 = 3 1 | | 205 | | |

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

^{*1} Guaranteed by design, not subject to production testing.

^{*2} Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time.

Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

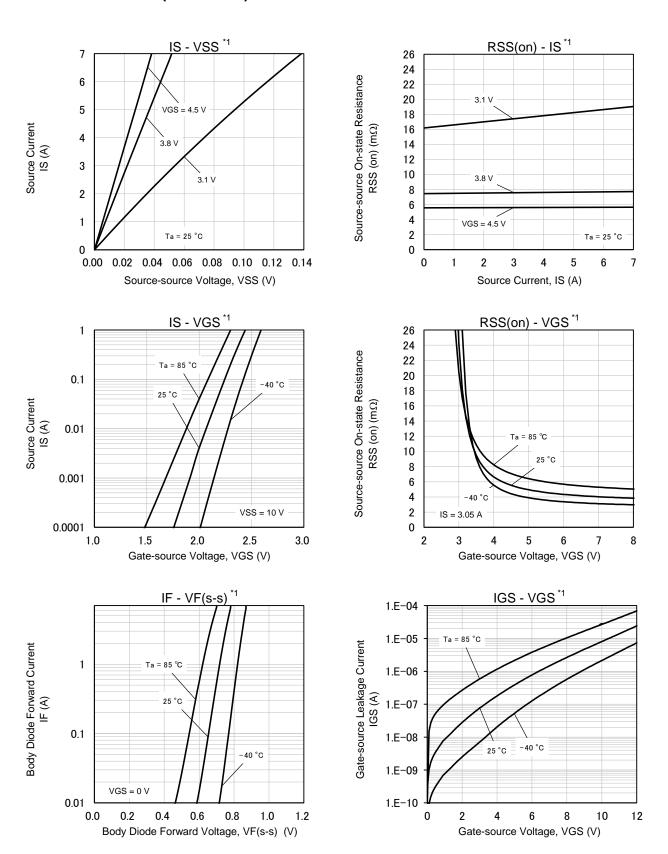


8. ELECTROSTATIC DISCHARGE CHARACTERISTIC Ta = 25 °C ± 3 °C

| Standard | Test Type | Symbol | Conditions | Class | Value | Unit |
|--------------|------------------|--------|---|-------|--------------|------|
| AEC-Q101-001 | Human Body Model | HBM | $C = 100 \text{ pF}, R = 1.5 \text{ k}\Omega$ | H1B | > 0.5 to ≤ 1 | kV |

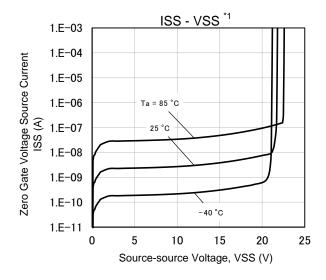


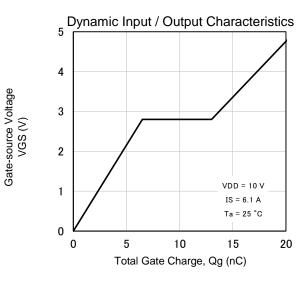
9. TECHNICAL DATA (Reference)

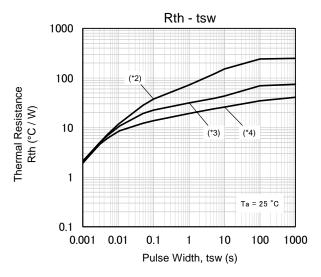


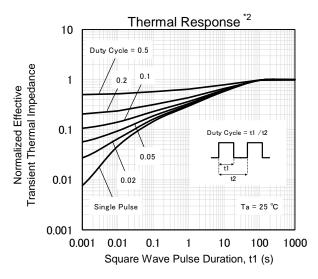


TECHNICAL DATA (Reference)







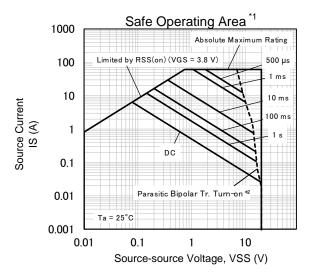


Note

- *1 Pulse measurement.
- *2 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board partially covered with copper pad (22 mm² area, 36 µm thickness).
- *3 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board fully covered with copper pad (602 mm² area, 36 µm thickness).
- *4 Mounted on ceramic board (70 mm x 70 mm x t1.0 mm).

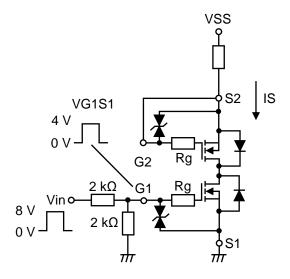


TECHNICAL DATA (Reference)



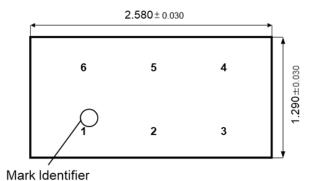
Note

- *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm). FR4 board partially covered with copper pad (22 mm² area, 36 µm thickness).
- *2 Measurement circuit for Parasitic Bipolar Tr. Turn-on.



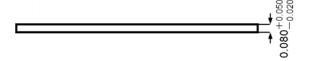
10. OUTLINE

(Top View)

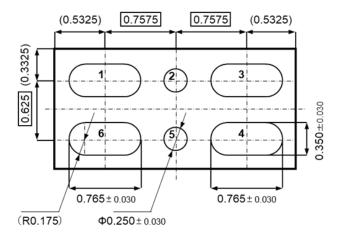


Unit: mm

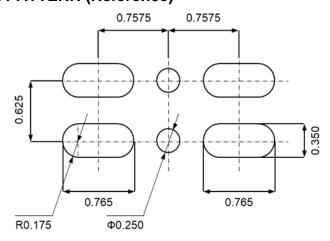
(Front View)



(Bottom View)



11. LAND & STENCIL PATTERN (Reference)



Unit: mm

Important notice:

Solder Mask Defined (SMD) pattern is strongly recommended for pad design.

Please check the information in the Nuvoton WL-CSP Application Notes about mounting process.



12. REVISION HISTORY

| Date | Revision | Description | | | |
|------------|----------|--|--|--|--|
| 2021.06.09 | 1.00 | 1. Initially issued. | | | |
| 2021.08.31 | 1.01 | 1. Added important notice in Land Pattern. | | | |
| | 1.01 | 2. Added special attention and precautions notes. | | | |
| 2021.11.11 | 1.02 | Changed document name from Product Standards to Datasheet. | | | |



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